
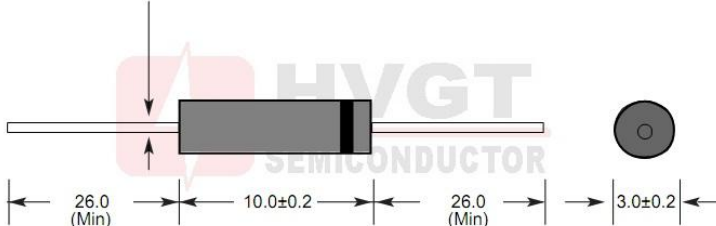




| | |
|--|---|
| INTRODUCE: | SHAPE DISPLAY: |
| HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers. |  <p>SIZE: (Unit:mm) : HVGT NAME: DO-310</p> <p>DO-310 Series Lead Diameter 0.6±0.03</p>  <p style="text-align: center;">Unit:mm</p> |
| FEATURES: | |
| <ol style="list-style-type: none"> High reliability design. High voltage design. High frequency . Conform to RoHS. Epoxy resin molded in vacuumHave anticorrosion in the surface. | |
| APPLICATIONS: | |
| <ol style="list-style-type: none"> High voltage multiplier circuit Electrostatic generator circuit . General purpose high voltage rectifier. Other. | |
| MECHANICAL DATA: | |
| <ol style="list-style-type: none"> Case: epoxy resin molding. Terminal: welding axis. Net weight: 0.28 grams (approx). | |

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

| Items | Symbols | Condition | Data Value | Units |
|--------------------------------------|-----------|---|------------|-------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | $T_A=25^{\circ}C$ | 14 | kV |
| | V_{RSM} | $T_A=25^{\circ}C$ | 17 | kV |
| Average Forward Current Maximum | I_{FVM} | $T_A=25^{\circ}C$ | 5.0 | mA |
| Suege Current | I_{FSM} | $T_A=25^{\circ}C$; Half-Sine Wave; 8.3mS | 0.5 | A |
| Junction Temperature | T_J | | -40~+125 | $^{\circ}C$ |
| Allowable Operation Case Temperature | T_C | | 125 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | | -40~+125 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

| Items | Symbols | Condition | Data value | Units |
|-------------------------------|----------|--|------------|---------|
| Maximum Forward Voltage Drop | V_F | at $25^{\circ}C$; at $I_{F(AV)}$ | 51 | V |
| Maximum Reverse Current | I_{R1} | at $25^{\circ}C$; at V_{RRM} | 2.0 | μA |
| | I_{R2} | at $100^{\circ}C$; at V_{RRM} | 5.0 | μA |
| Maximum Reverse Recovery Time | T_{RR} | at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FVM}$; $I_{RR}=0.25I_R$ | 80 | nS |
| Junction Capacitance | C_J | at $25^{\circ}C$; $V_R=0V$; $f=1MHz$ | 1.0 | pF |



Fig1

Forward Characteristics

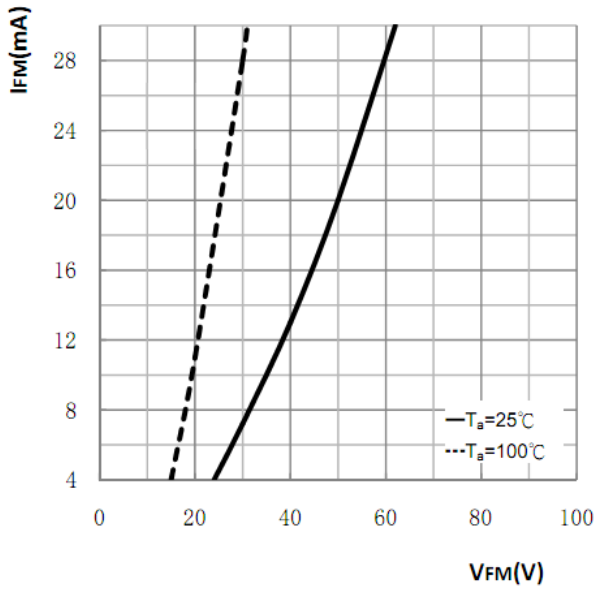


Fig2

Reverse Characteristics

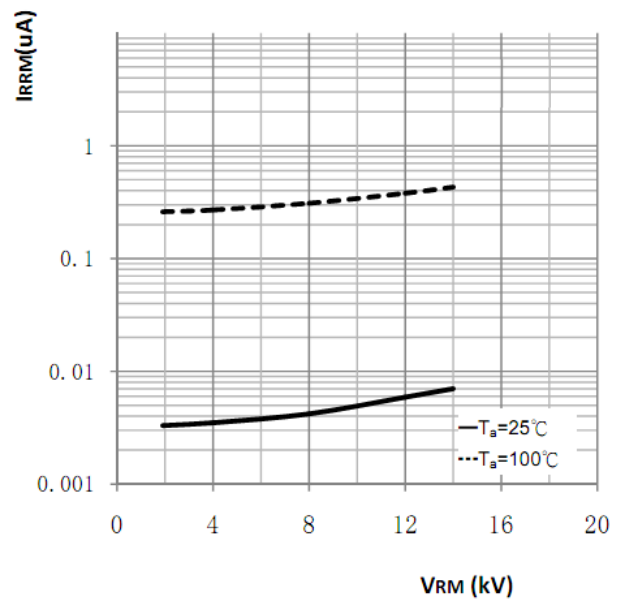


Fig3

VR-IF(AV) Curve

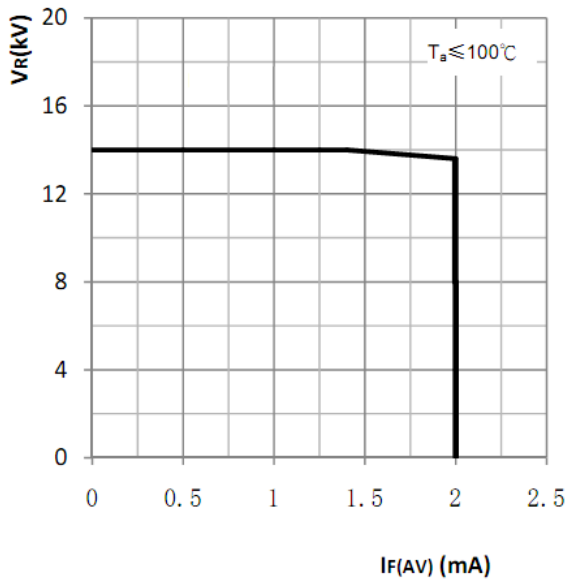
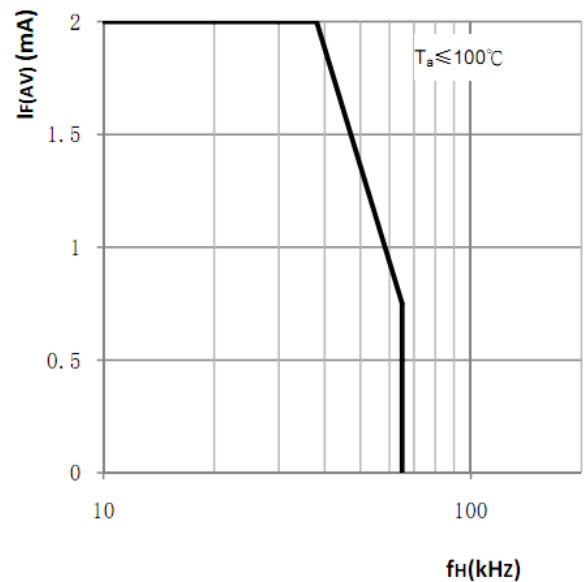


Fig4

IF(AV)-fH Curve



Marking

Type

HV-T74

Code

T74

Cathode Mark

